



# DCR2040L42

# **Phase Control Thyristor**

Replaces DS5960-3 DS5960-4 October 2023 (LN42843)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
DCR2040L42 DCR2040L40 DCR2040L35	4200 4000 3500	Tvj = -40°C to 125°C, IDRM = IRRM = 200mA, VDRM, VRRM tp = 10ms VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR2040L42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

$\mathbf{V}_{DRM}$	4200V
I <sub>T(AV)</sub>	2040A
Ітѕм	29000A
dV/dt*	1500V/µs
dl/dt	400A/μs

<sup>\*</sup> Higher dV/dt selections are available on request

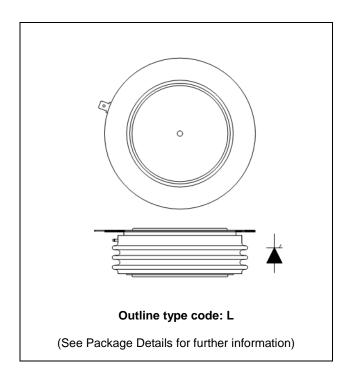


Fig. 1 Package outline

www.dynexsemi.com 1/10



## **CURRENT RATINGS**

## T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	2040	А
IT(RMS)	RMS value	-	3200	А
lτ	Continuous (direct) on-state current	-	2970	А

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	29.0	kA
l²t	I2t for fusing	V <sub>R</sub> = 0	4.21	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	Min.	Max.	Units	
		Double side cooled	DC	-	11.7	°C/kW
Rth(j-c) Thermal resist	Thermal resistance - junction to case	Cinale side socied	Anode DC	-	18.6	°C/kW
		Single side cooled	Cathode DC	-	32.9	°C/kW
Rth(c-h)	The second are interest and the state in large	Clamping force 37kN	Double side	-	2.5	°C/kW
	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	5.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			33	41	kN

www.dynexsemi.com 2/10



## **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	200	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.80	2.15	٧
dV/dt	Max. linear rate of rise of off-state voltage	To 67% VDRM, Tj = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub> Gate source 30V, 10Ω	Repetitive 50Hz	-	200	A/µs
di/dt	Trate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	400	A/µs
Vzza	Threshold voltage - Low level	500A to 2300A at Tcase = 125°C		-	0.90	V
<b>V</b> т(то)	Threshold voltage - High level	2300A to 7000A at Tcase = 125°C		-	1.08	٧
_	On-state slope resistance - Low level	500A to 2300A at Tcase = 125°C		-	0.35	mΩ
ľΤ	On-state slope resistance - High level	2300A to 7000A at Tcase = 1	-	0.27	mΩ	
tgd	Delay time	$V_D$ = 67% $V_{DRM}$ , gate source 30V, 10Ω $t_T$ = 0.5 $\mu$ s, $T_j$ = 25°C		-	3	μs
tq	Turn-off time	Tj = 125°C, VR = 200V, dI/dt = 1A/μs, dV <sub>DR</sub> /dt = 20V/μs linear		250	500	μs
Qs	Stored charge	Iτ = 2000A, Tj = 125°C, dl/dt = 1A/μs,		1050	2530	μC
IRR	Reverse recovery current	VR(peak) ~ 2500V, VRM ~ 1700V		27	42	А
lL	Latching current	Tj = 25°C, VD = 5V	-	3	А	
Ін	Holding current	Tj = 25°C, Rg-κ = ∞, Iтм = 50	0A, Iτ = 5A	-	300	mA

www.dynexsemi.com 3/10



### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
<b>V</b> GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V <sub>GD</sub>	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
lgт	Gate trigger current	VDRM = 5V, Tcase = 25°C	350	mA
IGD	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

## **CURVES**

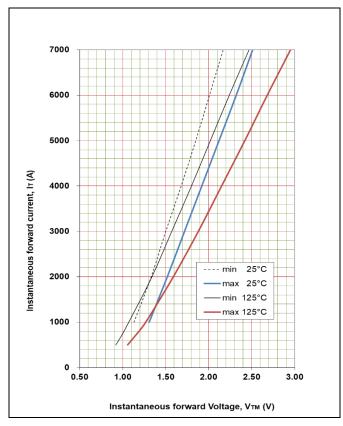


Fig. 2 Maximum & minimum on-state characteristics

## **VTM EQUATION**

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.121814

B = 0.135310

C = 0.000245

D = -0.001130

These values are valid for  $T_j = 125^{\circ}C$  for  $I_{T}$  500A to 7000A

www.dynexsemi.com 4/10



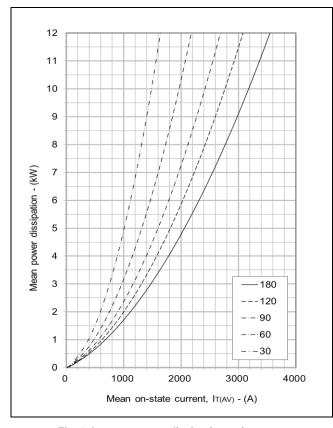


Fig. 3 On-state power dissipation - sine wave

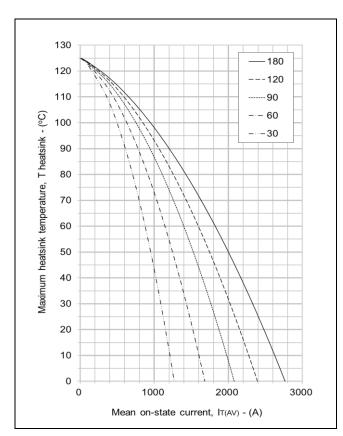


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

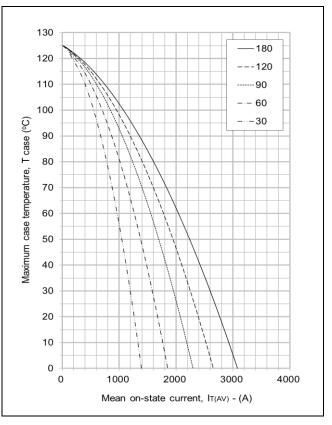


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

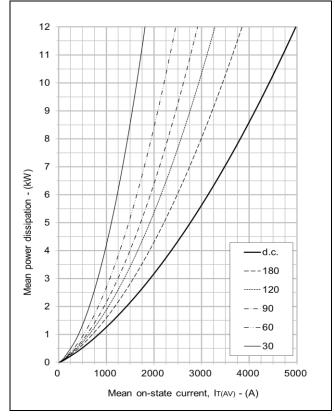


Fig. 6 On-state power dissipation - rectangular wave

www.dynexsemi.com 5/10



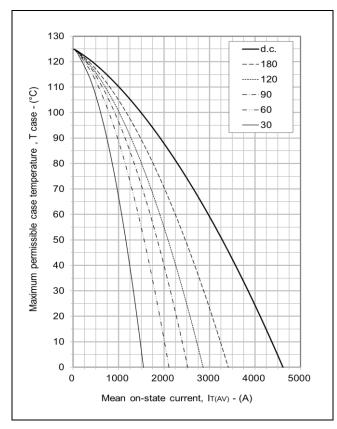
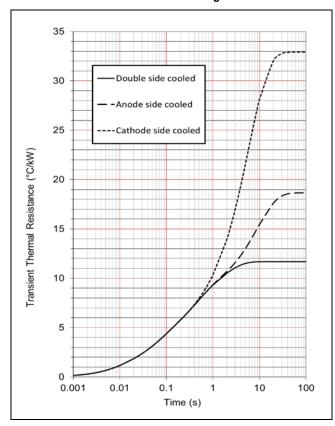


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



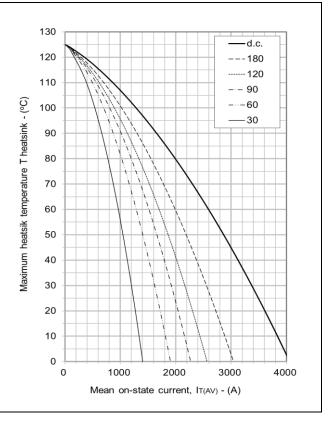


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.834	2.607	4.207	4.041
cooled	Ti(s)	0.009	0.053	0.331	1.612
Anode side	Ri(°C/kW)	0.965	2.831	4.943	9.909
cooled	Ti(s)	0.010	0.063	0.420	8.908
Cathode side	Ri(°C/kW)	0.929	2.937	2.358	26.683
cooled	Ti(s)	0.009	0.062	0.309	5.853

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

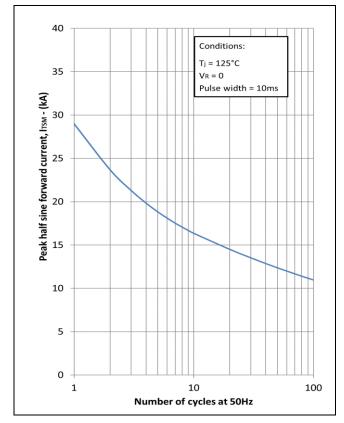
Tables show the increments of thermal resistance R  $_{\text{th}(j-c)}$  when the device operates at conduction angles other than d.c.

	Double side cooling			Anode Side Cooling			Ca	thode Side	d Cooling			
	∆Z <sub>ft</sub> (	(z)		$\Delta Z_{t_1}(z)$		$\Delta Z_{f_1}(z)$		$\Delta Z_{fi}(z)$			$\Delta Z_i$	<sub>h</sub> (Z)
θ°	sine.	rect.	6	,	sine.	rect.	θ°	sine.	rect.			
180	1.45	0.98	18	0	1.43	0.97	180	1.44	0.97			
120	1.68	1.40	12	0	1.66	1.39	120	1.66	1.39			
90	1.93	1.64	9	0	1.90	1.62	90	1.91	1.63			
60	2.16	1.90	6	0	2.12	1.88	60	2.14	1.89			
30	2.34	2.19	3	0	2.30	2.15	30	2.31	2.17			
15	2.42	2.34	1	5	2.37	2.30	15	2.39	2.31			

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

www.dynexsemi.com 6/10





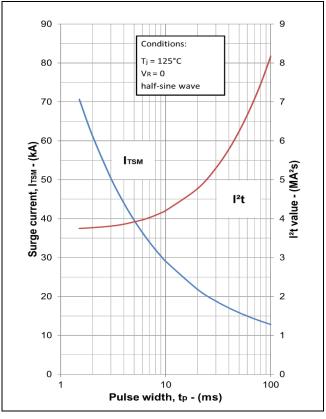


Fig. 10 Multi-cycle surge current

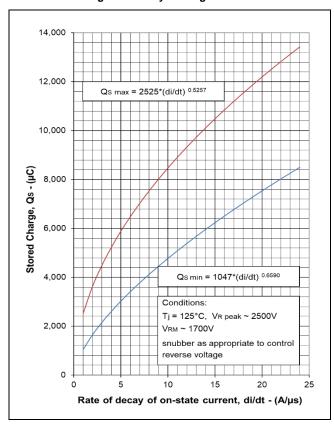


Fig. 12 Reverse recovery charge

Fig. 11 Single-cycle surge current

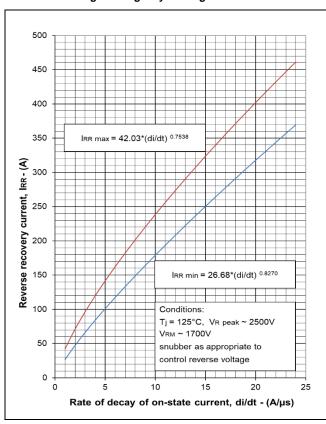


Fig. 13 Reverse recovery current

www.dynexsemi.com 7/10



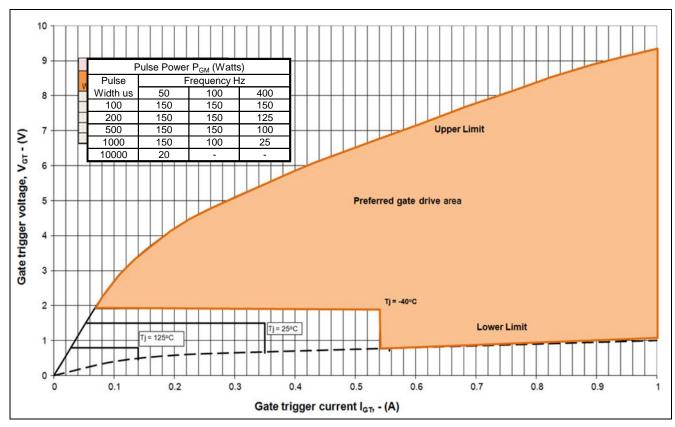


Fig. 14 Gate characteristics

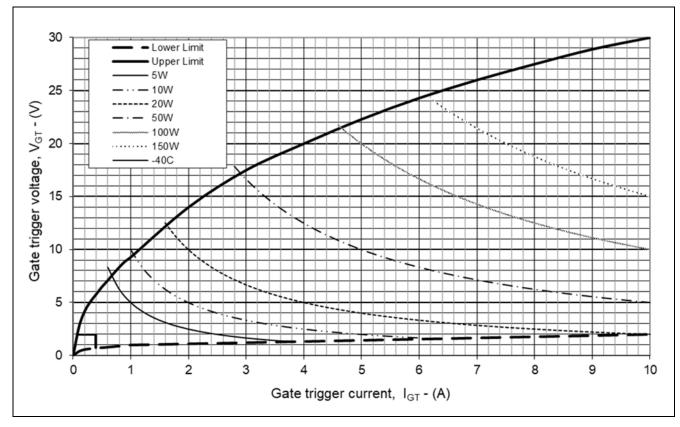


Fig. 15 Gate characteristics

www.dynexsemi.com 8/10



### **PACKAGE DETAILS**

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

### DO NOT SCALE

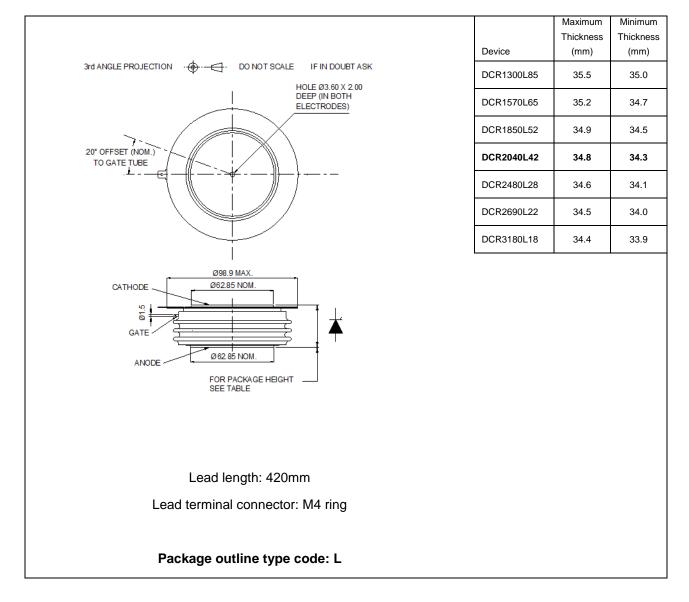


Fig. 16 Package outline

www.dynexsemi.com 9/10



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www.dynexsemi.com 10/10